

## KVR1066D3E7K2/4G

4GB (2GB 2Rx8 256M x 72-Bit x 2 pcs.)

PC3-8500 CL7 ECC 240-Pin DIMM Kit

**Important Information:** The module defined in this data sheet is one of several configurations available under this part number. While all configurations are compatible, the DRAM combination and/or the module height may vary from what is described here.

### DESCRIPTION

ValueRAM's KVR1066D3E7K2/4G is a kit of two 256M x 72-bit (2GB) DDR3-1066 CL7 SDRAM (Synchronous DRAM), 2Rx8 ECC memory modules, based on eighteen 128M x 8-bit FBGA components per module. Total kit capacity is 4GB. The SPD's are programmed to JEDEC standard latency DDR3-1066 timing of 7-7-7 at 1.5V. Each 240-pin DIMM uses gold contact fingers. The electrical and mechanical specifications are as follows:

### FEATURES

- JEDEC standard 1.5V (1.425V ~1.575V) Power Supply
- VDDQ = 1.5V (1.425V ~ 1.575V)
- 533MHz fCK for 1066Mb/sec/pin
- 8 independent internal bank
- Programmable CAS Latency: 8, 7, 6
- Programmable Additive Latency: 0, CL - 2, or CL - 1 clock
- Programmable CAS Write Latency(CWL) = 6 (DDR3-1066)
- 8-bit pre-fetch
- Burst Length: 8 (Interleave without any limit, sequential with starting address "000" only), 4 with tCCD = 4 which does not allow seamless read or write [either on the fly using A12 or MRS]
- Bi-directional Differential Data Strobe
- Internal(self) calibration: Internal self calibration through ZQ pin (RZQ : 240 ohm  $\pm$  1%)
- On Die Termination using ODT pin
- Average Refresh Period 7.8us at lower than TCASE 85°C, 3.9us at 85°C < TCASE  $\leq$  95°C
- Asynchronous Reset
- PCB: Height 1.18" (30mm), double sided component

### SPECIFICATIONS

|                                                  |                       |
|--------------------------------------------------|-----------------------|
| CL(IDD)                                          | 7 cycles              |
| Row Cycle Time (tRCmin)                          | 50.63ns (min.)        |
| Refresh to Active/Refresh Command Time (tRFCmin) | 110ns (min.)          |
| Row Active Time (tRASmin)                        | 37.5ns (min.)         |
| Power (Operating)                                | 1.890 W* (per module) |
| UL Rating                                        | 94 V - 0              |
| Operating Temperature                            | 0° C to 85° C         |
| Storage Temperature                              | -55° C to +100° C     |

\*Power will vary depending on the SDRAM used.

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